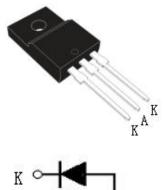
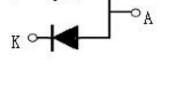


FRED Ultrafast Soft Recovery Diode, 12A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction





Product Summary		
VR	200V	
lf(AV)	6*2A	
trr	20ns	

Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings				
Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	Vrrm		200	V
Continuous forward current	lf(AV)	Tc =110°C	12	
Single pulse forward current	IFSM	Tc =25°C	72	А
Maximum repetitive forward current	IFRM	Square wave, 20kHZ	64	
Operating junction	Тј		175	°C
Storage temperatures	Tstg		-55 to +175	°C

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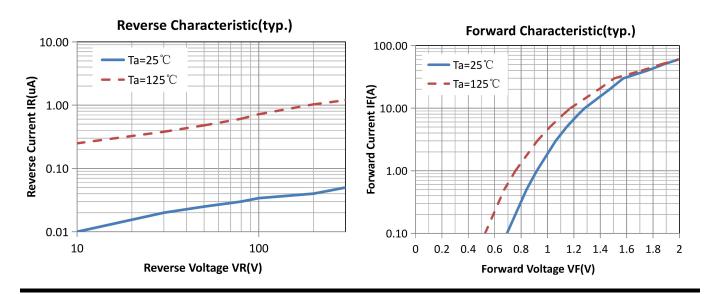


Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units
Breakdown voltage	VBR,	Ir=100μA	200			
Blocking voltage	V _R					
Forward voltage (Per Diode)	.,	IF=6A		0.9	1.1	V
	VF	IF=6A, Tj =125°C		0.8	1.0	
Reverse leakage current(Per Diode)	VR= VRRM			10	_	
	Tj=150°C, Vr=200V			100	μΑ	
Reverse recovery time(Per Diode)		I _F =0.5A, I _R =1A, I _{RR} =0.25A		25	35	
	Trr	I _F =1A,V _R =30V, di/ <i>dt</i> =200A/us		20	30	ns

Thermal characteristics

Paramter	Symbol	Тур	Units
Junction-to-Case	$R_{ heta JC}$	4.2	°C/W

Electrical performance (typic)

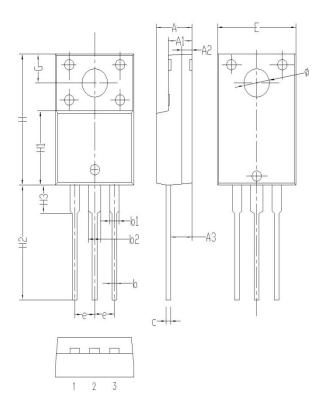


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Package Information

TO-220FPA PACKAGE



Symbol	Dimensions(millimeters)		
Symbol	Min.	Max.	
Α	4.30	4.70	
A1	2.80	3.20	
A2	1.10	1.50	
A3	2.50	2.90	
b	0.50	0.75	
b1	1.10	1.35	
b2	1.50	1.75	
С	0.45	0.75	
е	2.34	2.7	
E	9.85	10.45	
Н	14.8	15.0	
H1	8.30	8.70	
H2	12.7	13.7	
H3	3.10	3.50	
G	2.50	2.90	
Φ P	3.10	3.40	

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